

DIGITRON SEMICONDUCTORS

MAC213 SERIES

SILICON BIDIRECTIONAL THYRISTORS

Available Non-RoHS (standard) or RoHS compliant (add PBF suffix).

Available as "HR" (high reliability) screened per MIL-PRF-19500, JANTX level. Add "HR" suffix to base part number.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak repetitive off-state voltage ⁽¹⁾ (T _J = -40 to +125°C) MAC213-4 MAC213-6 MAC213-8 MAC213-10	V _{DRM}	200 400 600 800	Volts
Peak gate voltage	V _{GM}	10	Volts
RMS on-state current (full sine wave, 50 to 60Hz, T _C = 85°C)	I _{T(RMS)}	12	Amps
Peak non-repetitive surge current (1 cycle, 60 Hz, T _C = 85°C, preceded and followed by rated current)	I _{TSM}	100	Amps
Circuit fusing considerations (T _C = 85°C, t = 1.0 to 8.3ms)	I ² t	41	A ² s
Peak gate power (T _C = 85°C, pulse width = 10µs)	P _{GM}	20	Watts
Average gate power (T _C = 85°C, t = 8.3ms)	P _{G(AV)}	0.35	Watts
Peak gate current (T _C = 85°C, pulse width = 10µs)	I _{GM}	2.0	Amps
Operating junction temperature range	T _J	-40 to +125	°C
Storage temperature range	T _{stg}	-40 to +150	°C

Note 1: Ratings apply for open gate conditions. Thyristor devices shall not be tested with a constant current source for blocking capability such that the voltage applied exceeds the rated blocking voltage.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Maximum	Unit
Thermal resistance, junction to case	R _{θJC}	2.1	°C/W

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ.	Max	Unit
Peak blocking current (either direction) (V _D = Rated V _{DRM} @ T _J = 25°C) (V _D = Rated V _{DRM} @ T _J = 125°C)	I _{DRM}	-	-	10 2	µA mA
Peak on-state voltage (either direction) (I _{TM} = 17A peak, pulse width = 1 to 2 ms, duty cycle ≤ 2%)	V _{TM}	-	1.3	1.75	Volts
Gate trigger current (continuous dc) (main terminal voltage = 12V, R _L = 100Ω) MT2(+),G(+) MT2(+),G(-) MT2(-),G(-)	I _{GT}	-	-	100 100 100	mA
Gate trigger voltage (continuous dc) (main terminal voltage = 12V, R _L = 100Ω) MT2(+),G(+) MT2(+),G(-) MT2(-),G(-) (main terminal voltage = Rated V _{DRM} , R _L = 10kΩ, T _J = 125°C) MT2(+), G(+); MT2(-), G(-); MT2(+), G(-)	V _{GT}	-	-	2 2 2	Volts
		0.2	-	-	

DIGITRON SEMICONDUCTORS

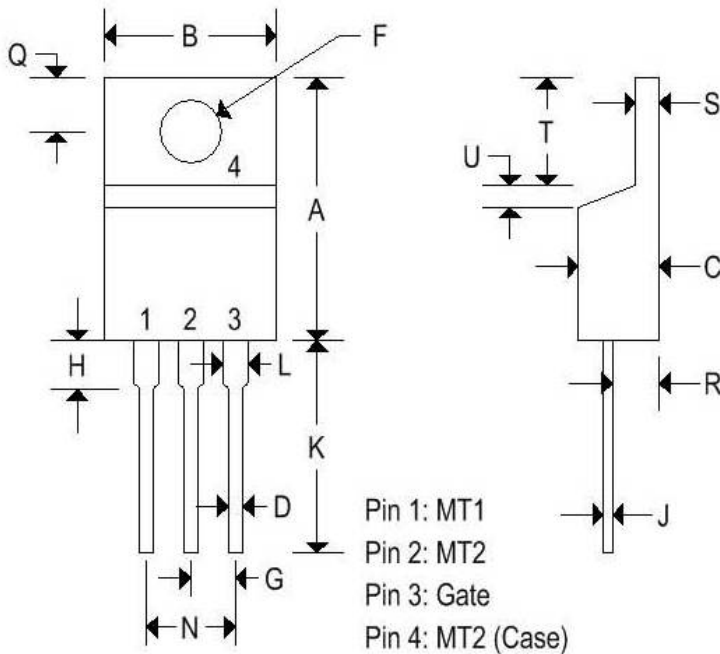
MAC213 SERIES

SILICON BIDIRECTIONAL THYRISTORS

Characteristic	Symbol	Min	Typ.	Max	Unit
Holding current (either direction) (main terminal voltage= 12V, gate open, initiating current = 200mA, T _c = 25°C)	I _H	-	-	100	mA
Turn on time (Rated V _{DRM} , I _{TM} = 17A, I _{GT} = 120mA, rise time = 0.1μs, pulse width = 2μs)	t _{gt}	-	1.5	-	μs
Critical rate of rise of off-state voltage (V _D = Rated V _{DRM} , exponential voltage rise, gate open, T _c = 25°C) (V _D = Rated V _{DRM} , exponential voltage rise, gate open, T _c = 125°C)	dv/dt	500 200	- -	- -	V/μs

MECHANICAL CHARACTERISTIC

Case	TO-220AB
Marking	Body painted, alpha-numeric
Pin out	See below



	TO-220AB			
	Inches		Millimeters	
	Min	Max	Min	Max
A	0.575	0.620	14.600	15.750
B	0.380	0.405	9.650	10.290
C	0.160	0.190	4.060	4.820
D	0.025	0.035	0.640	0.890
F	0.142	0.147	3.610	3.730
G	0.095	0.105	2.410	2.670
H	0.110	0.155	2.790	3.930
J	0.014	0.022	0.360	0.560
K	0.500	0.562	12.700	14.270
L	0.045	0.055	1.140	1.390
N	0.190	0.210	4.830	5.330
Q	0.100	0.120	2.540	3.040
R	0.080	0.110	2.040	2.790
S	0.045	0.055	1.140	1.390
T	0.235	0.255	5.970	6.480
U	-	0.050	-	1.270
V	0.045	-	1.140	-
Z	-	0.080	-	2.030

DIGITRON SEMICONDUCTORS

MAC213 SERIES SILICON BIDIRECTIONAL THYRISTORS

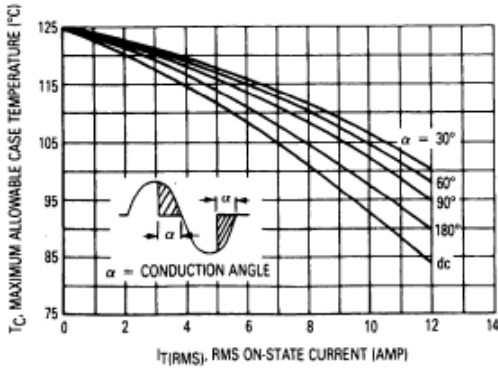


Figure 1. Current Derating

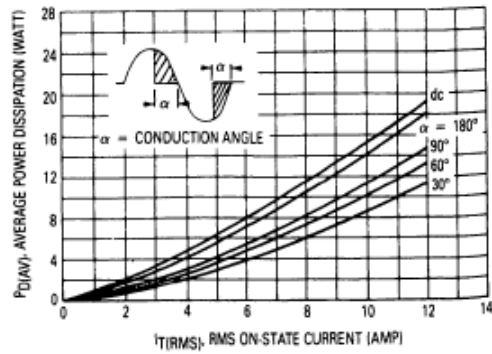


Figure 2. Power Dissipation

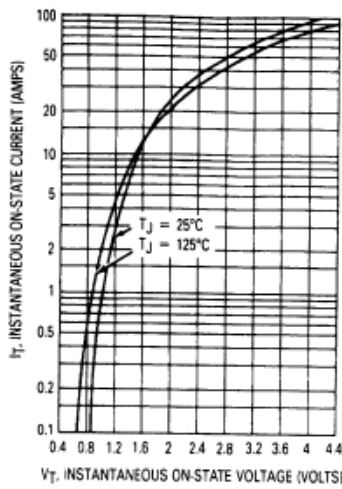


Figure 3. Maximum On-State Characteristics

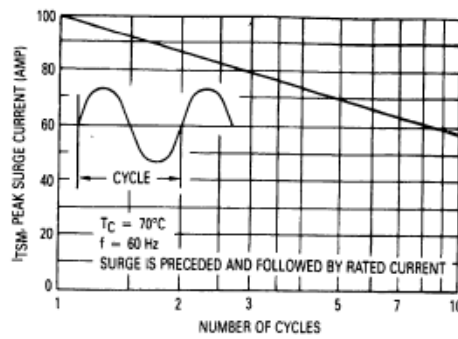


Figure 4. Maximum Non-Repetitive Surge Current

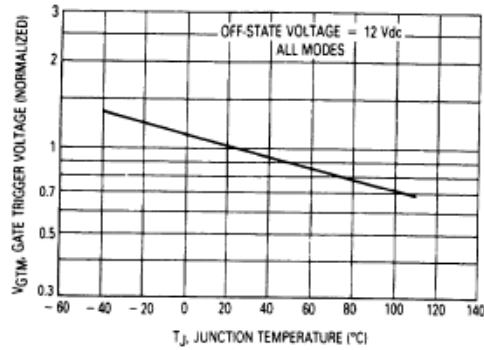


Figure 5. Typical Gate Trigger Voltage

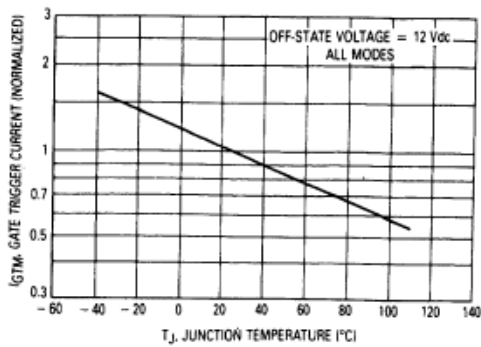


Figure 6. Typical Gate Trigger Current

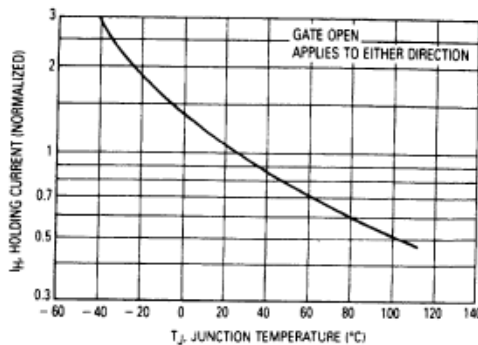


Figure 7. Typical Holding Current

DIGITRON SEMICONDUCTORS

MAC213 SERIES

SILICON BIDIRECTIONAL THYRISTORS

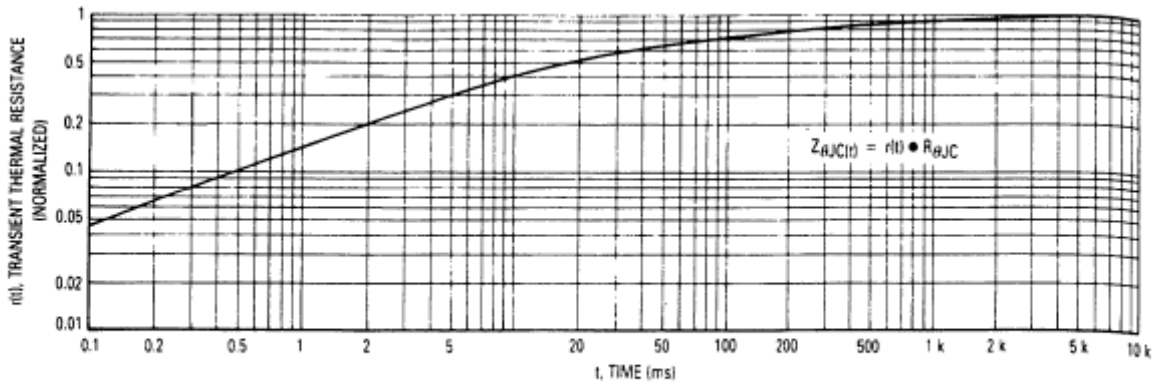


Figure 8. Thermal Response